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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **KANO, Takashi et al.**

Group Art Unit: **2812**

Serial No.: **09/941,982**

Examiner: **MULPURI, Savitri**

Filed: **August 30, 2001**

P.T.O. Confirmation No.: **7536**

For: **METHOD OF FORMING NITRIDE-BASED SEMICONDUCTOR LAYER, AND METHOD OF MANUFACTURING NITRIDE-BASED SEMICONDUCTOR DEVICE**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents  
Washington, D.C. 20231

November 27, 2002

Sir:

In response to the Office Action dated **June 28, 2002**, please amend the above identified application as follows:

IN THE CLAIMS:

Please cancel Claims 6 and 15 without prejudice or disclaimer.

Please amend Claims 1 and 10, as follows:

1. (Amended) A method of forming a nitride-based semiconductor layer, comprising the steps of:

growing a buffer layer of  $Al_xGa_{1-x}N$  ( $0 \leq X \leq 1$ ) on a substrate at a growth rate of at least  $7\text{ \AA/sec}$ ; and

growing a nitride-based semiconductor layer of  $A_1aB_bIn_cT1_dGa_{1-a-b-c-d}N$  ( $0 \leq a < 1, 0 \leq b < 1, 0 \leq c < 1, 0 \leq d < 1, a+b+c+d < 1$ ) on said buffer layer, wherein

said step of growing the buffer layer comprises growing said buffer layer to have a film thickness in the range from  $50\text{ \AA}$  to  $300\text{ \AA}$ .

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